FUJI ELECTRIC

2MBI 75L-120

2-Pack IGBT
1200 V
75 A

IGBT MODULE (L series)

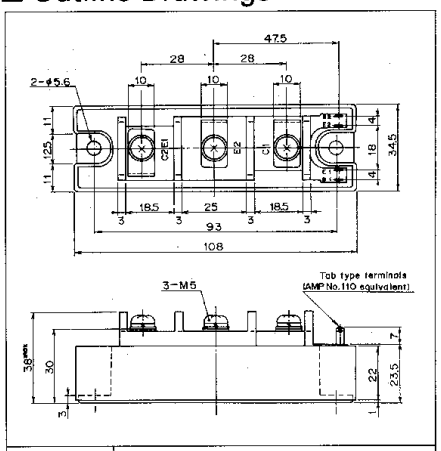
■ Features

- High Speed Switching
- Low Saturation Voltage
- Voltage Drive

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial Machines, such as Welding Machines

■ Outline Drawings



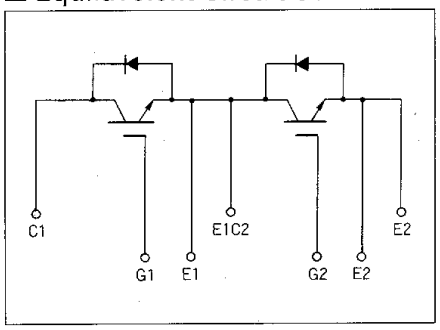
CASE	M216
UL	

■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings

Items		Symbols	Ratings	Units
Collecter-Emitter Voltage		V_{CES}	1200	V
Gate-Emitter Voltage		V_{GES}	±20	V
Collecter Current	Continuous	I_C	75	A
	1ms	$I_{C\ pulse}$	150	
	Continuous	$-I_C$	75	
	1ms	$-I_{C\ pulse}$	150	
Max. Power Dissipation		P_C	600	W
Operating Temperature		T_j	+150	°C
Storage Temperature		T_{stg}	–40 to +125	°C
Net. Weight			230	g
Isolation Voltage	AC. 1min.	V_{isol}	2500	V
Screw Torque		Mounting *1	35	kg•cm
		Terminals *2	35	

■ Equilavelent Circuit Schematic



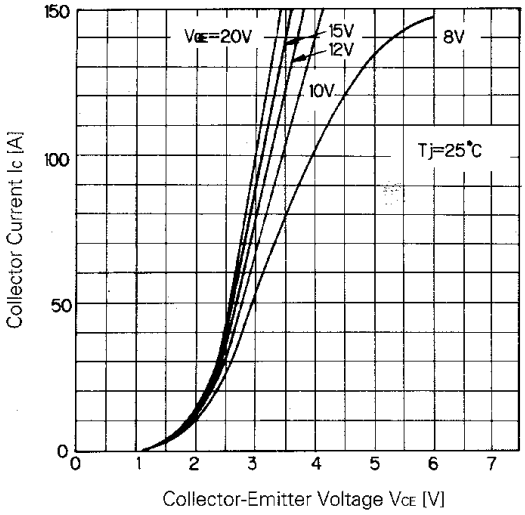
*1 Recommendable Value 25 to 35kg•cm (M5)
*2 Recommendable Value 25 to 35kg•cm (M5)

● Electrical Characteristics (Tc=25°C)

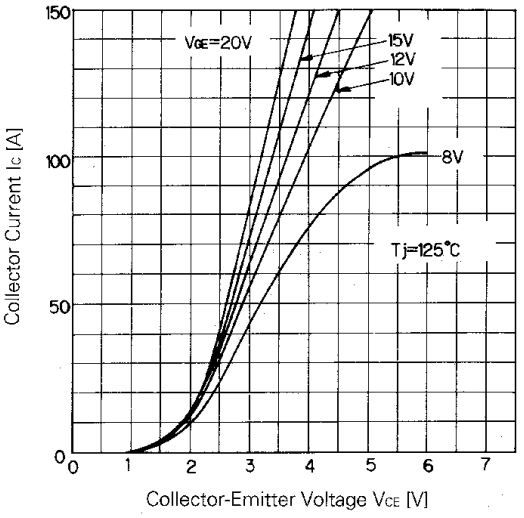
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collecter Current	I_{CES}	V_{GE}=0V V_{CE}=1200V T_c=25°C			1.0	mA
		V_{GE}=0V V_{CE}=1200V T_c=125°C			–	mA
Gate-Emitter Leackage Current	I_{GES}	V_{CE}=0V V_{GE}=±20V			100	nA
Gate-Emitter Threshold Voltage	$V_{GE\ (th)}$	V_{CE}=20V I_C=75mA	3.0		6.0	V
Collecter-Emitter Saturation Voltage	$V_{CE\ (sat)}$	V_{GE}=15V I_C=75A		2.7	3.5	V
Input Capacitance	Cies	V_{GE}=0V		13500		pF
Output Capacitance	Coes	V_{CE}=10V		–		
Reverse Transfer Capacitance	Cres	f=1MHz		–		
Turn-on Time	t_{on}	V_{CC}=600V		0.5	0.8	μs
	t_r	I_C=75A		0.3	0.6	
Turn-off Time	t_{off}	V_{GE}=±15V		0.8	1.5	
	t_f	R_G=16Ω		0.3	0.5	
Diode Forward On-Voltage	V_F	I_F=75A V_{GE}=0V			2.5	V
Reverse Recovery Time	t_{rr}	I_F=75A –di/dt=225A/μs V_{GE}=–10V		200	350	ns

● Thermal Characteristics

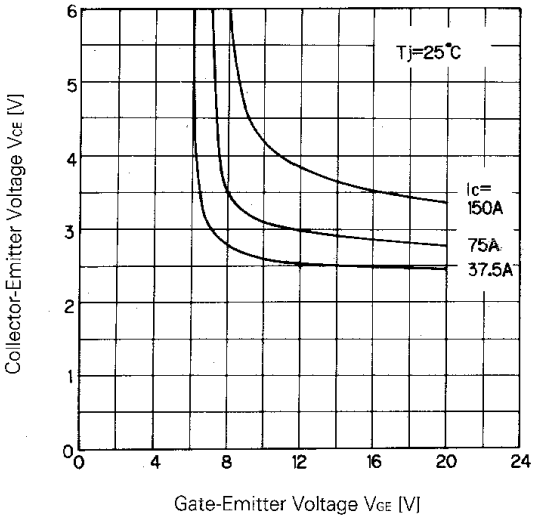
Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	$R_{th\ (j-c)}$	IGBT			0.208	°C/W
	$R_{th\ (j-c)}$	Diode			0.40	
	$R_{th\ (c-f)}$	With Thermal compound		0.05		



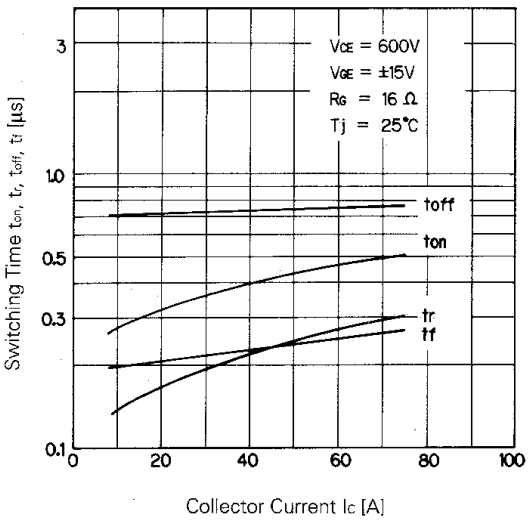
Collector Current vs. Collector-Emitter Voltage



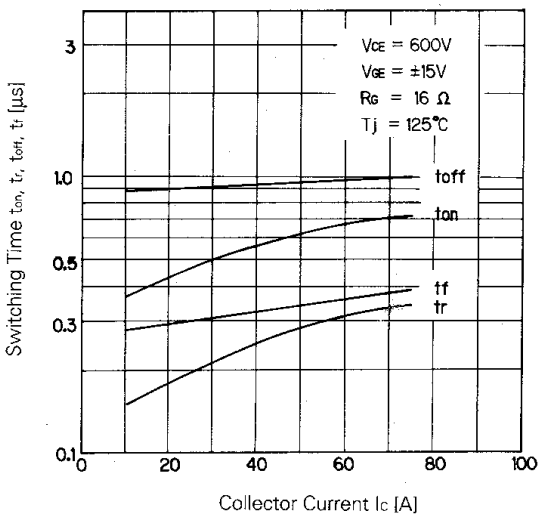
Collector Current vs. Collector-Emitter Voltage



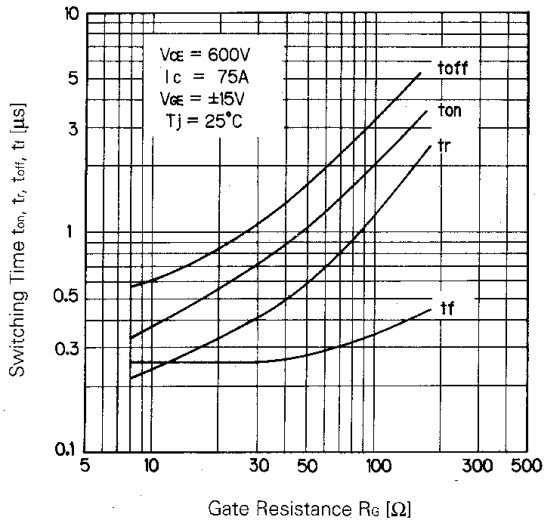
Collector-Emitter Voltage vs. Gate-Emitter Voltage



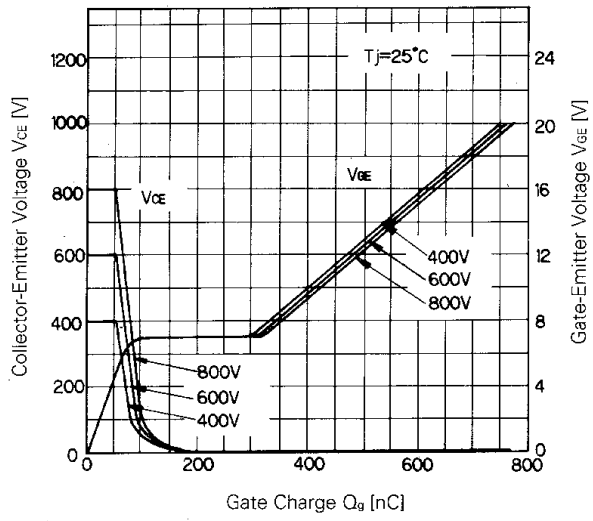
Switching Time



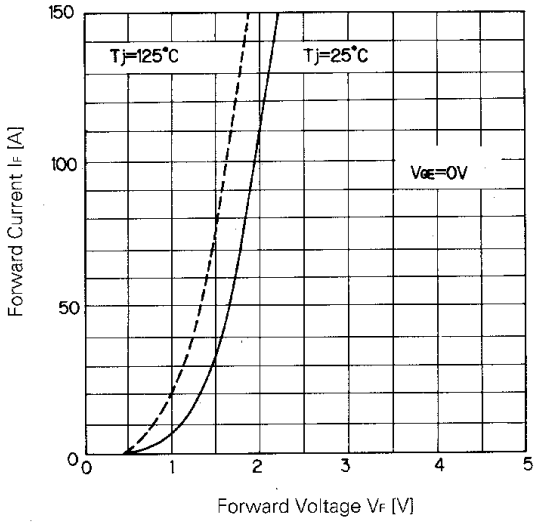
Switching Time



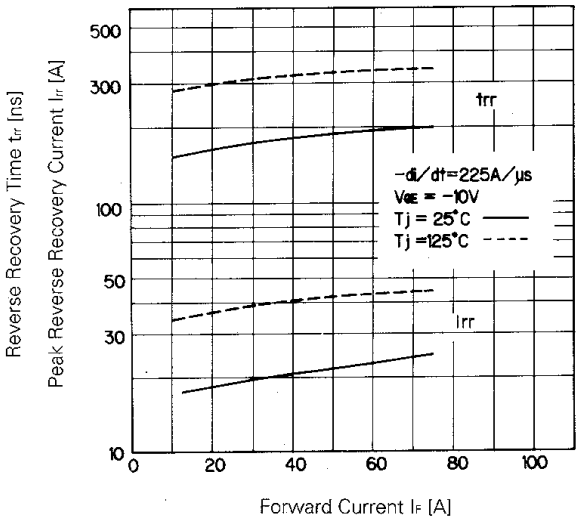
Switching Time-Gate Resistance



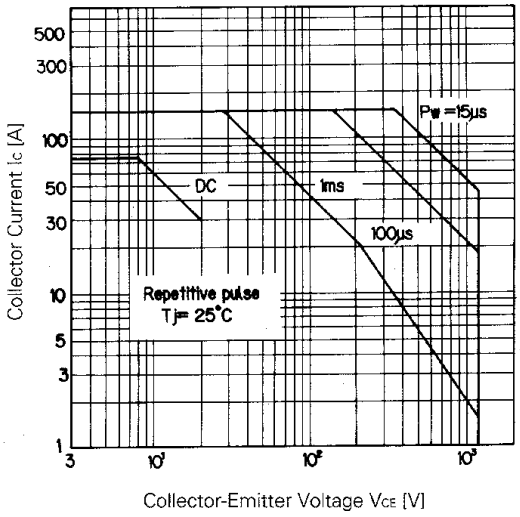
Dynamic Input Characteristic



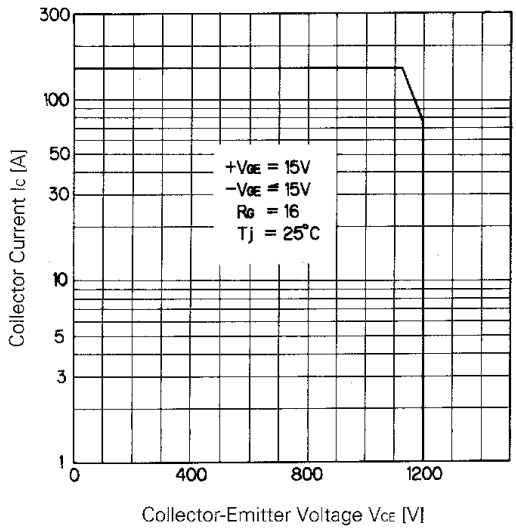
Forward Voltage of Free Wheel Diode



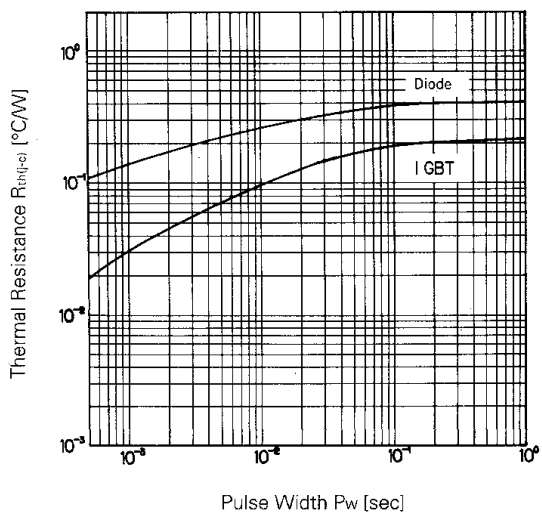
trr, Irr-IF



Safe Operating Area



Reverse Biased Safe Operating Area



Transient Thermal Resistance

For more information, contact:

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